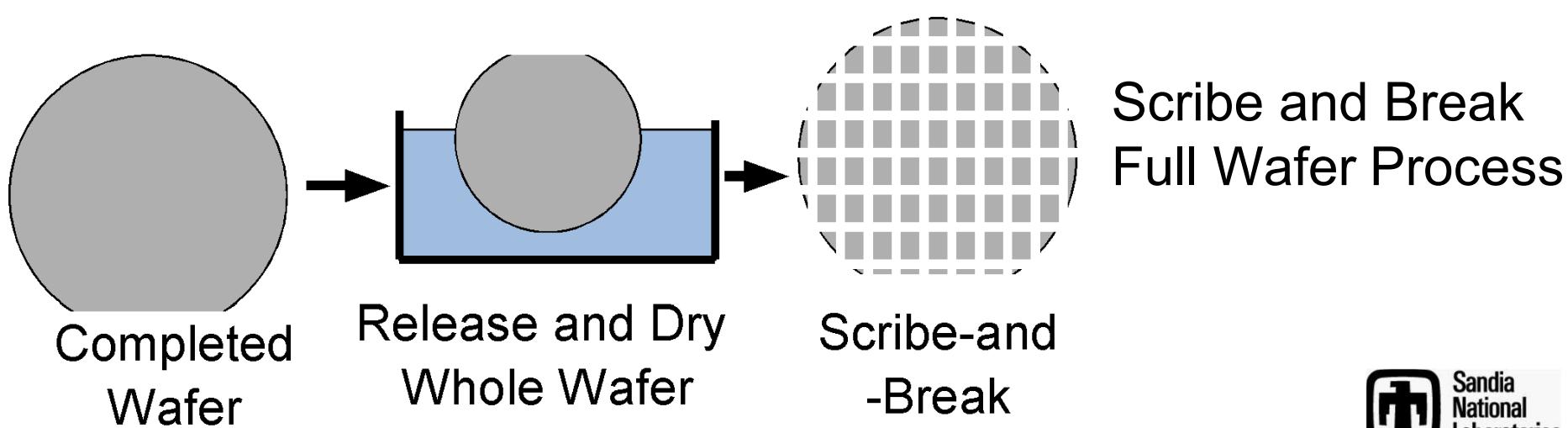
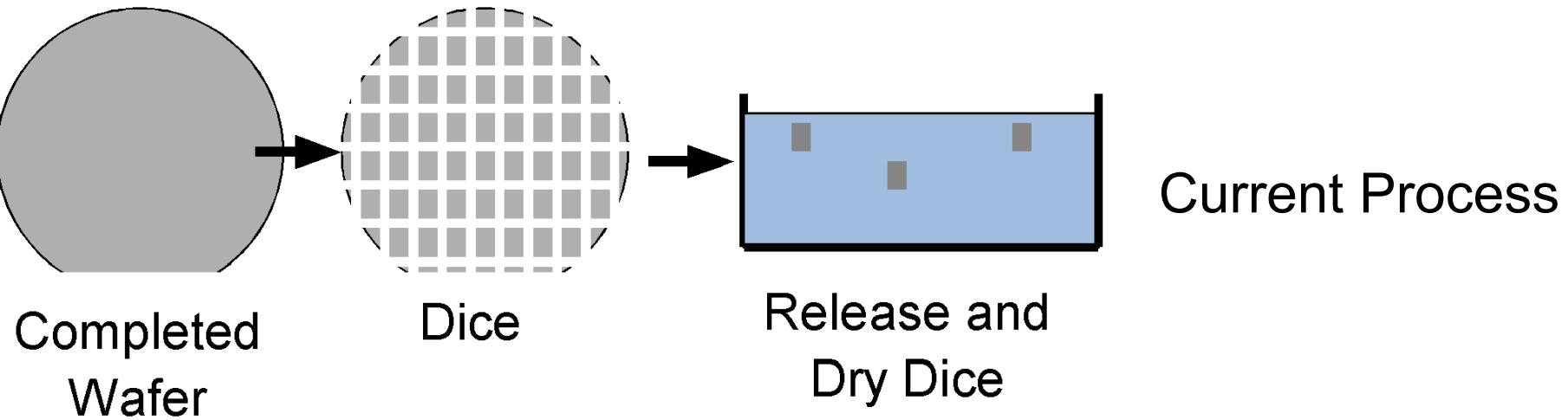


SCRIBE-AND-BREAK FOR POST RELEASE MEMS DIE SEPARATION

Andrew D. Oliver, Ph.D.
Advanced Microsystem Packaging
Sandia National Laboratories
adolive@sandia.gov
505 845-7931



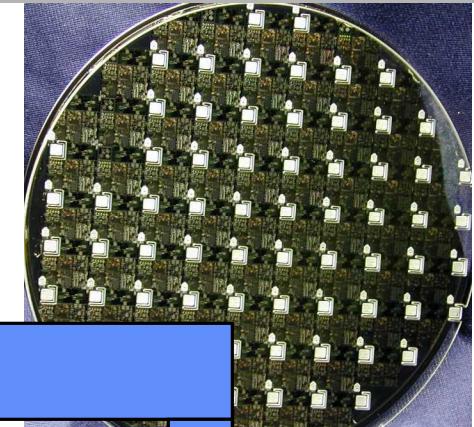
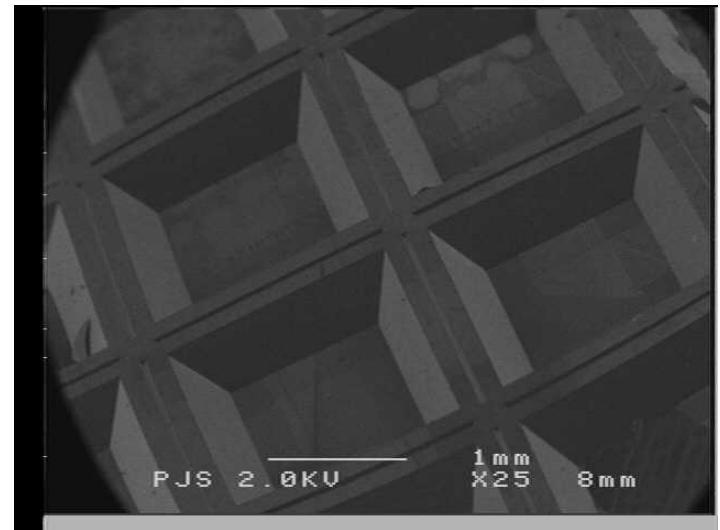
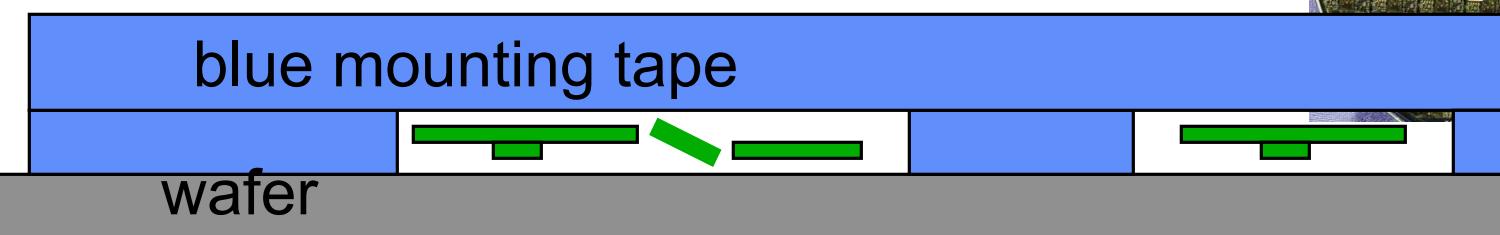
WHY POST RELEASE DIE SINGULATION FOR SURFACE MICROMACHINES?





APPROACHES

- Dice and then Release
 - Sandia
 - No process changes
- Permanent Cap
 - Motorola
 - Provides first level package but it changes the device and the process
- Temporary Cap
 - Analog Devices
 - Need to allocate real estate for the cap
 - Changes the Process
- Break after Release
 - Texas Instruments





CRITERIA AND CHOICES

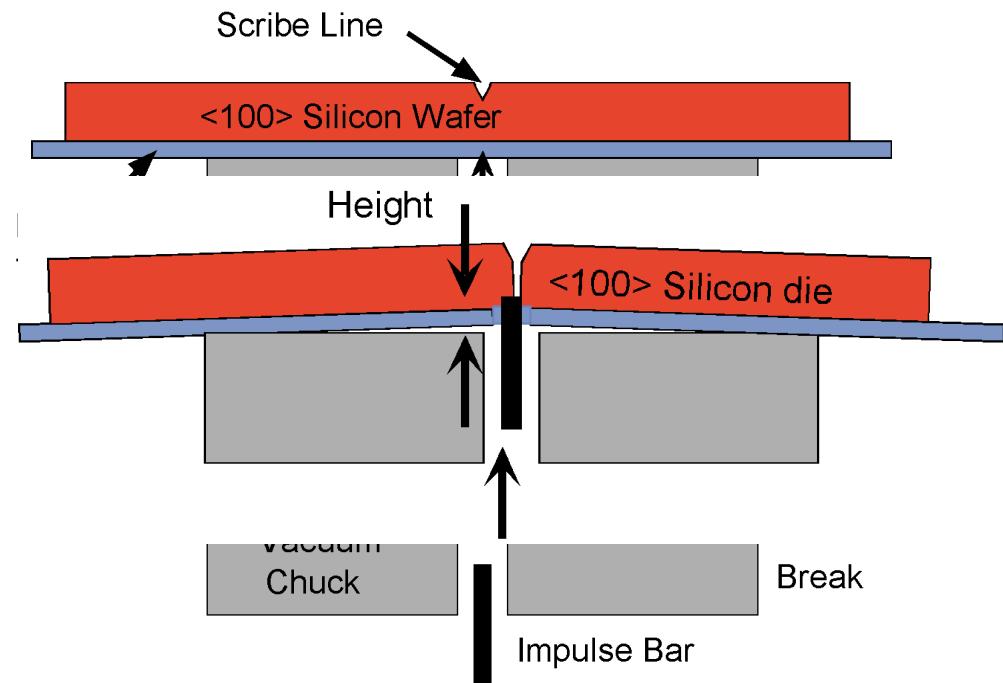
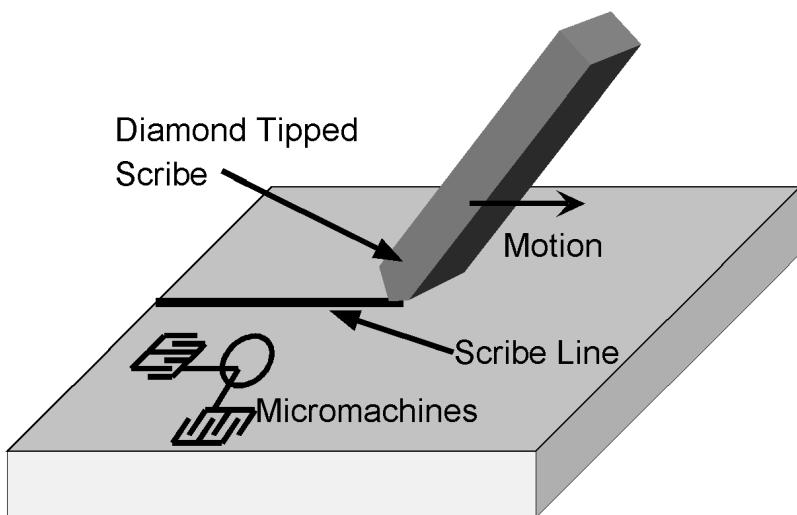
- **Process must be**
 - Dry
 - Particle free
 - Robust
- **Alternatives**
 - Analog Devices
 - Texas Instruments (partial saw and break)
 - Laser Cutting
 - Laser Scribing
 - Diamond Scribing



ADVANTAGES TO SCRIBE AND BREAK

- No process changes
- 100% of die size devoted to MEMS
- Transparent to designers
- Fast
- Low cost
- Disadvantage
 - Not well understood

SCRIBE AND BREAK



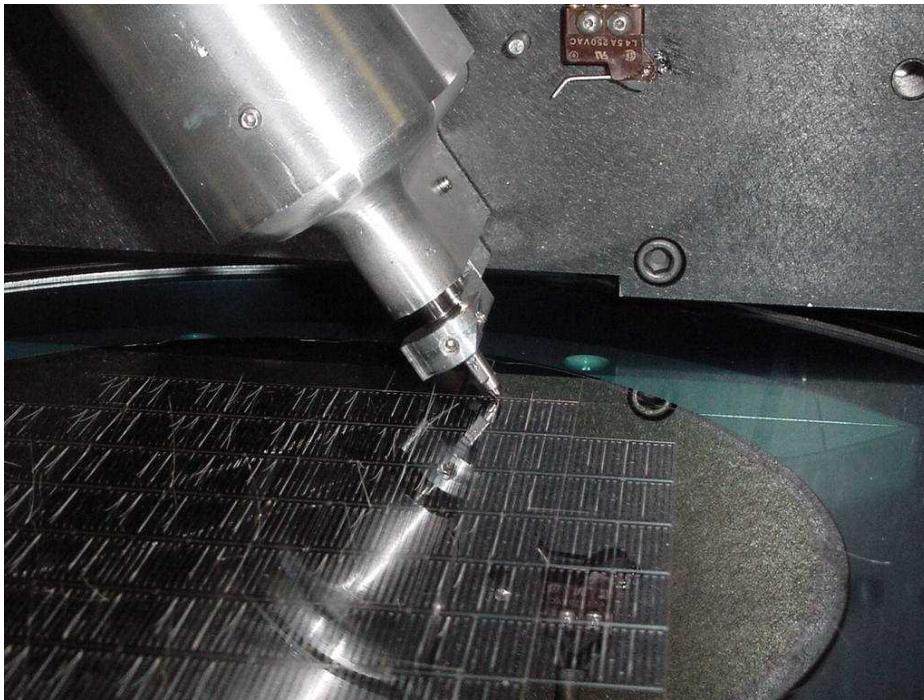
1. Released MEMS wafer is scored with a diamond scribe

2. Wafer is broken into die along scribe line

Post release die singulation enables full wafer release of MEMS devices



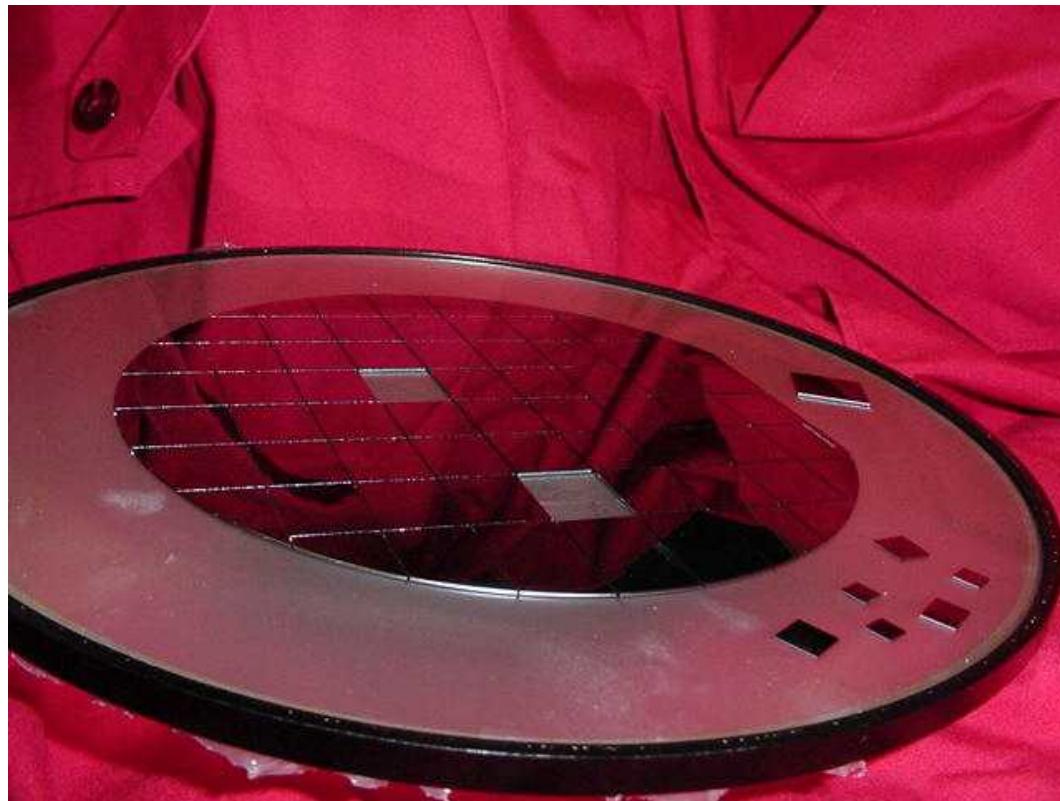
SCRIBE AND BREAK MACHINE



- GST Scriber/Breaker
- Manufactured by Dynatex International, Santa Rosa, California
- Handles substrates up to 150 mm in diameter



WAFERS MOUNTING



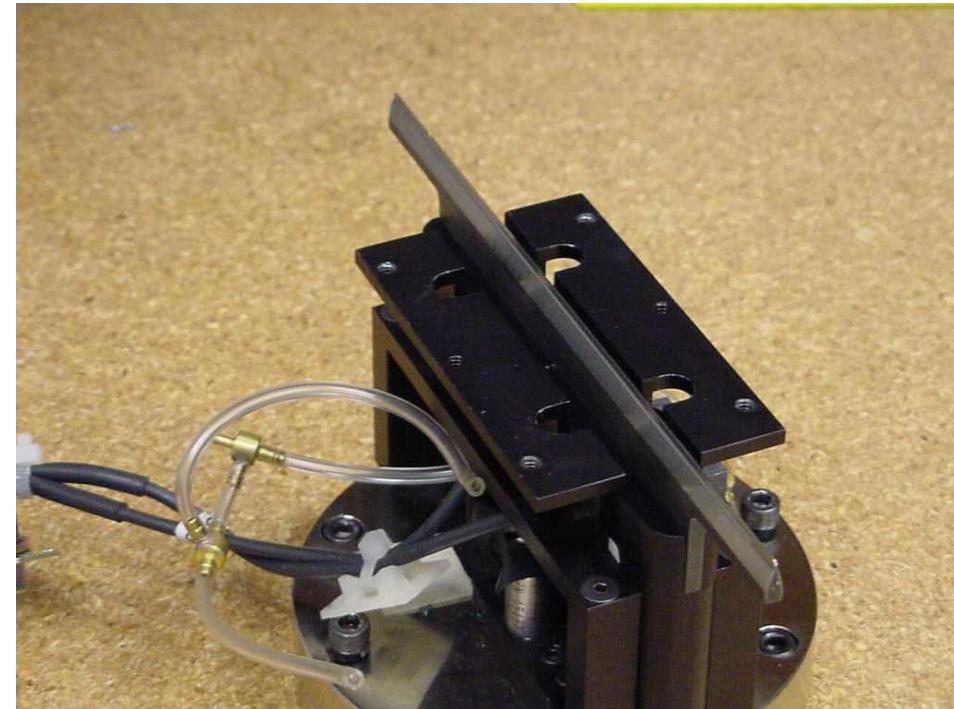
- Wafers mounted on frame before scribing (either standard or UV tape)



VACUUM CHUCK AND BREAKER



- Vacuum chuck

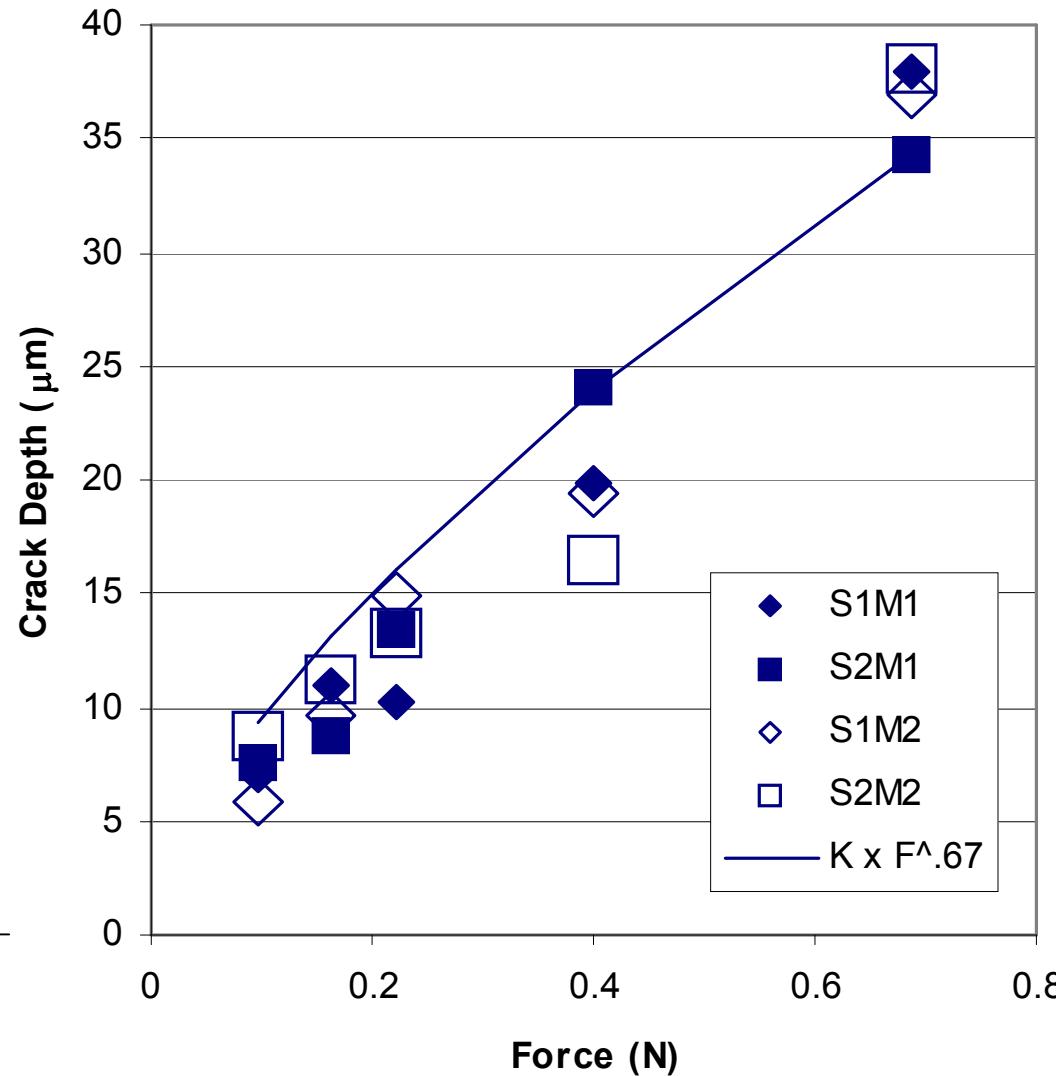


- Breaking bar

MEDIAN CRACK DEPTH

- Measurements were taken with 2 different SEMs on two different samples
- 4 samples total

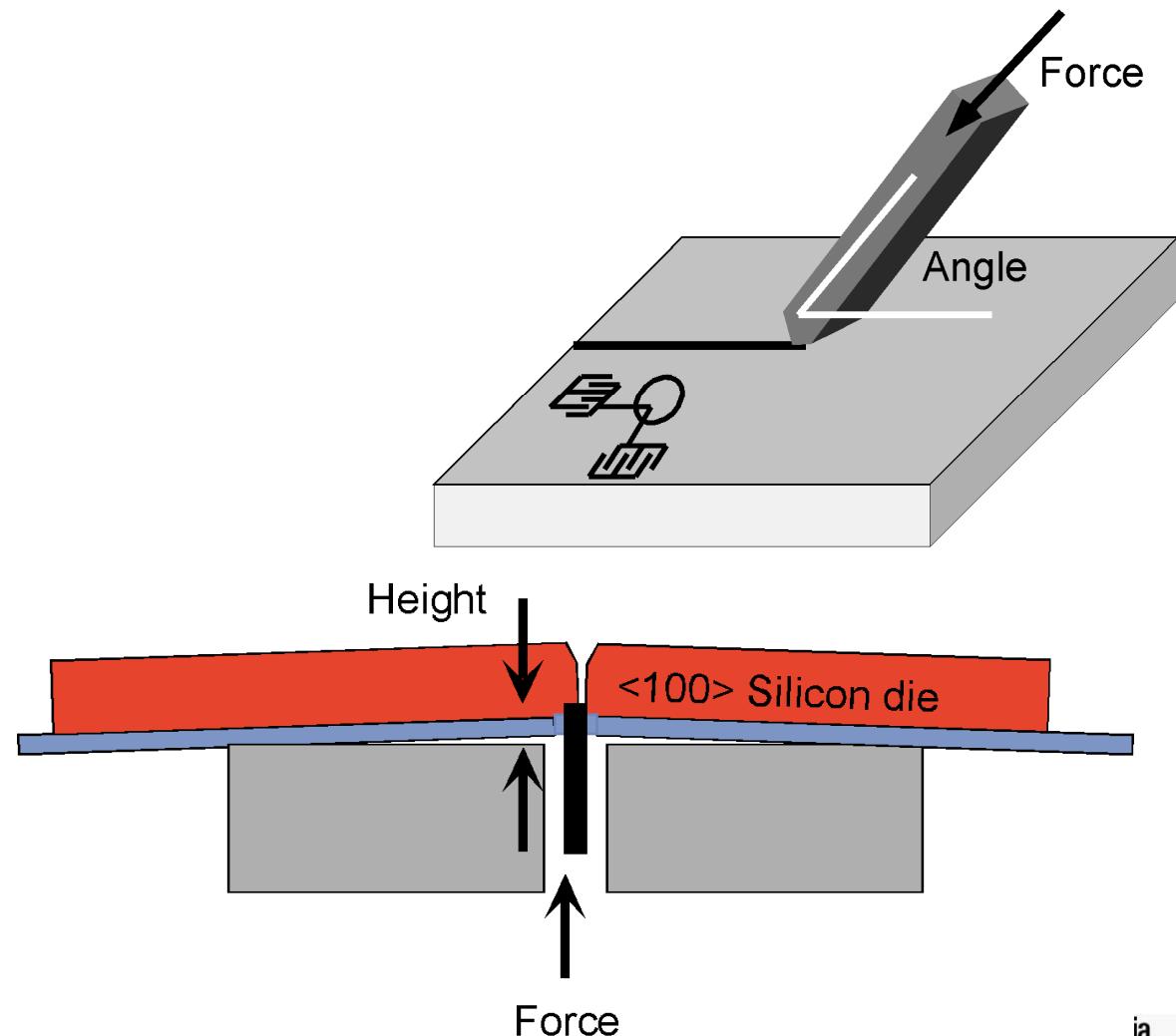
$$depth = \frac{\left(2CF/K_{IC}\right)^{2/3}}{\pi}$$





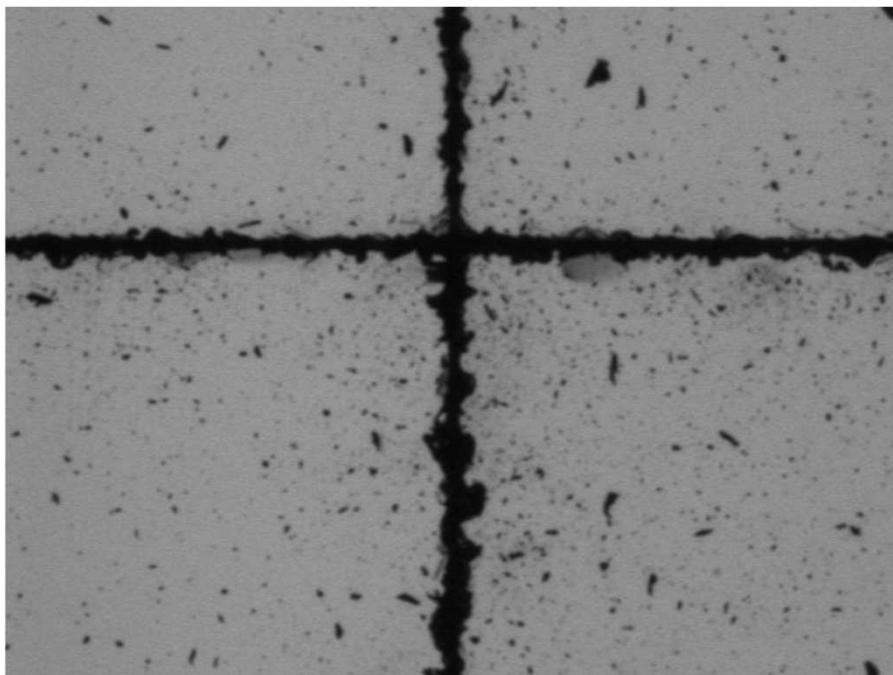
DESIGN OF EXPERIMENTS TO FIND PARAMETER IMPORTANCE

- Machine has 13 parameters
- 4 parameter full factorial
- Run 3 times in different orders
- Parameters used were scribe force, scribe angle, break pressure, and break height

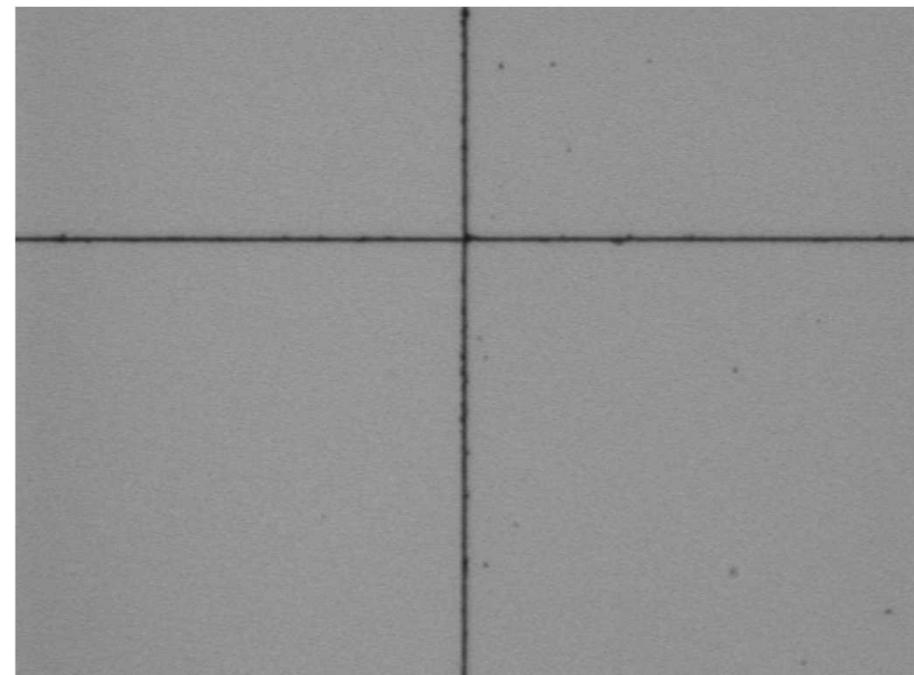




TO QUANTIFY SCRIBE QUALITY

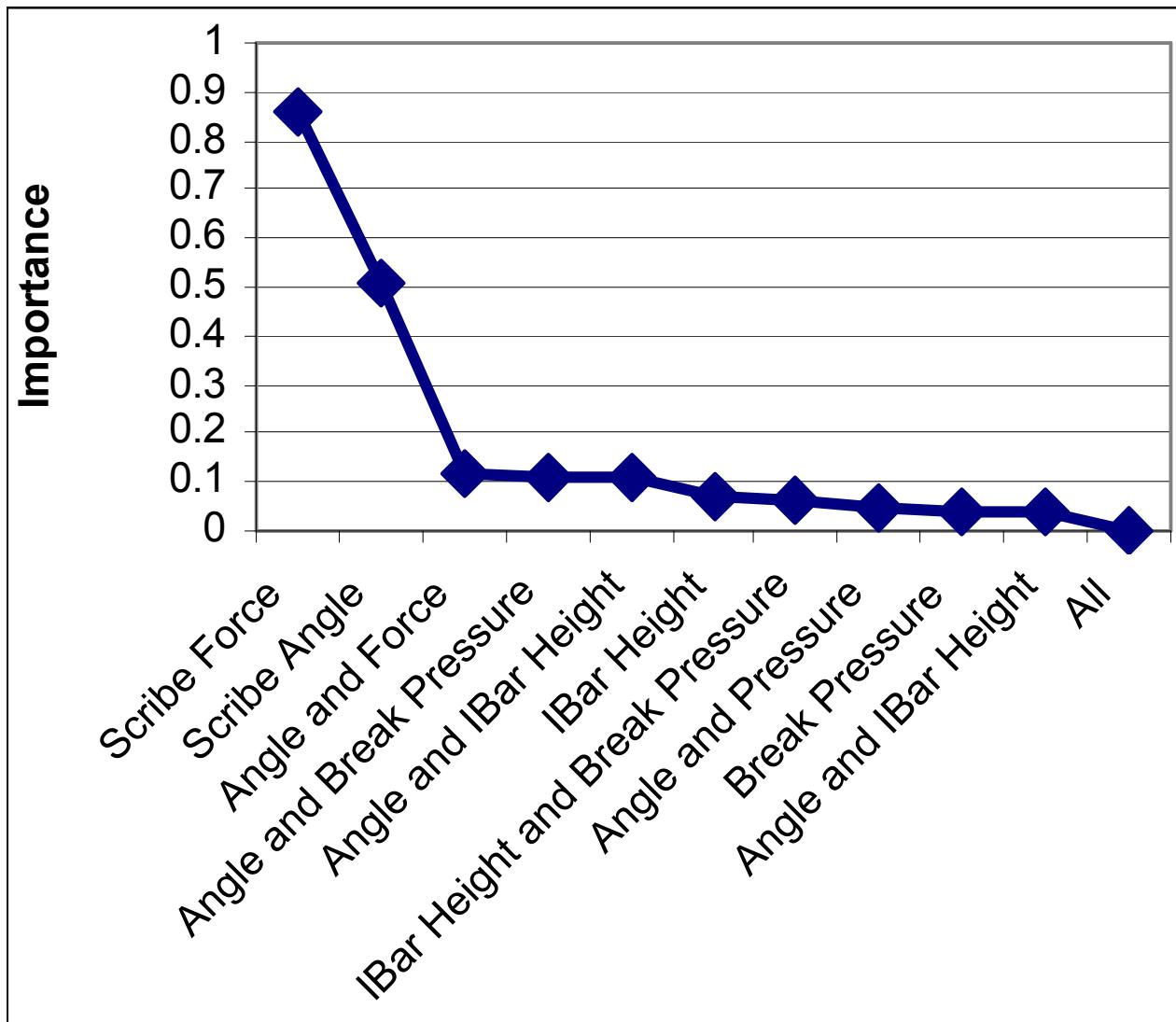


Quality 5 scribe



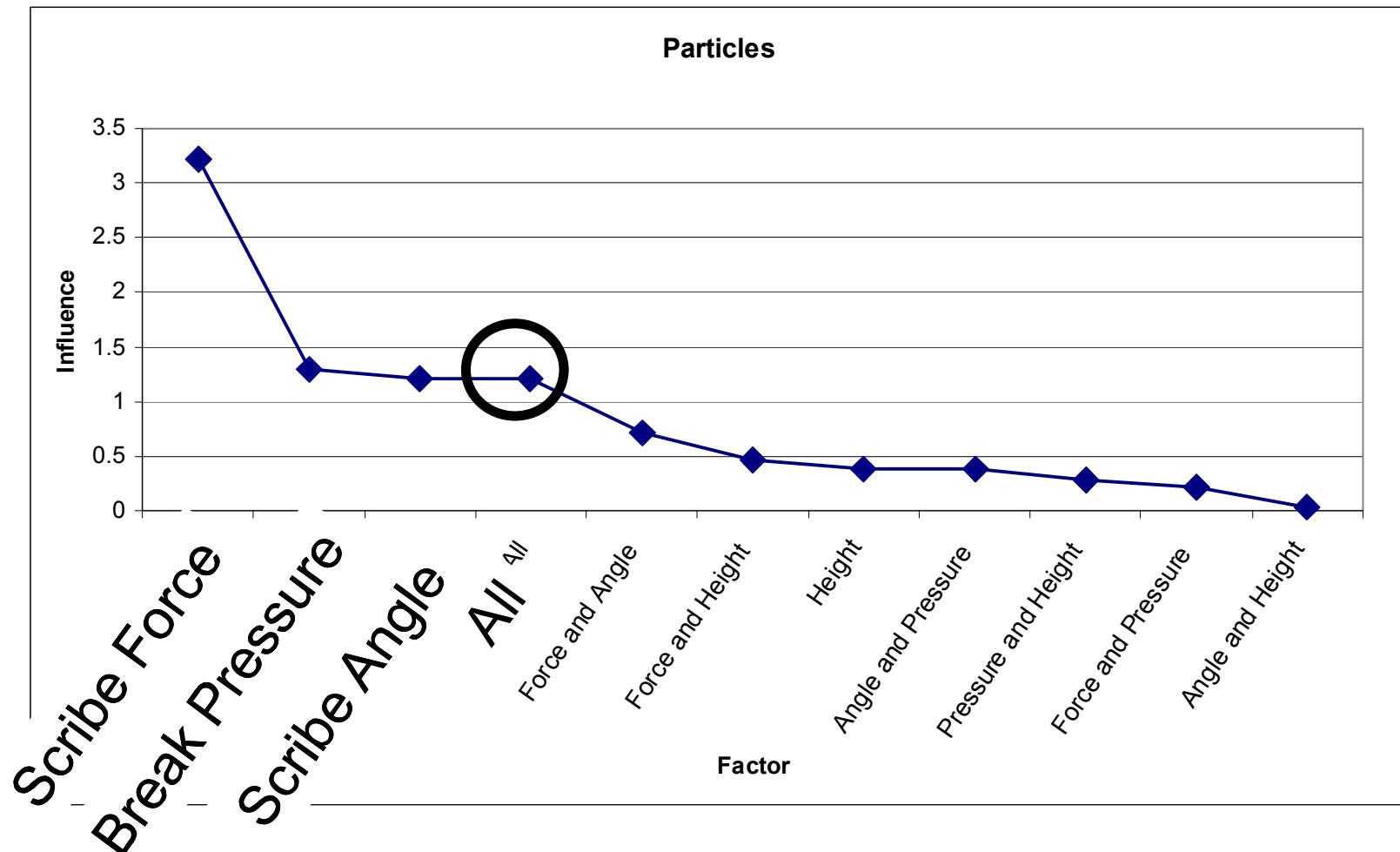
Quality 1 scribe

DESIGN OF EXPERIMENTS QUALITY



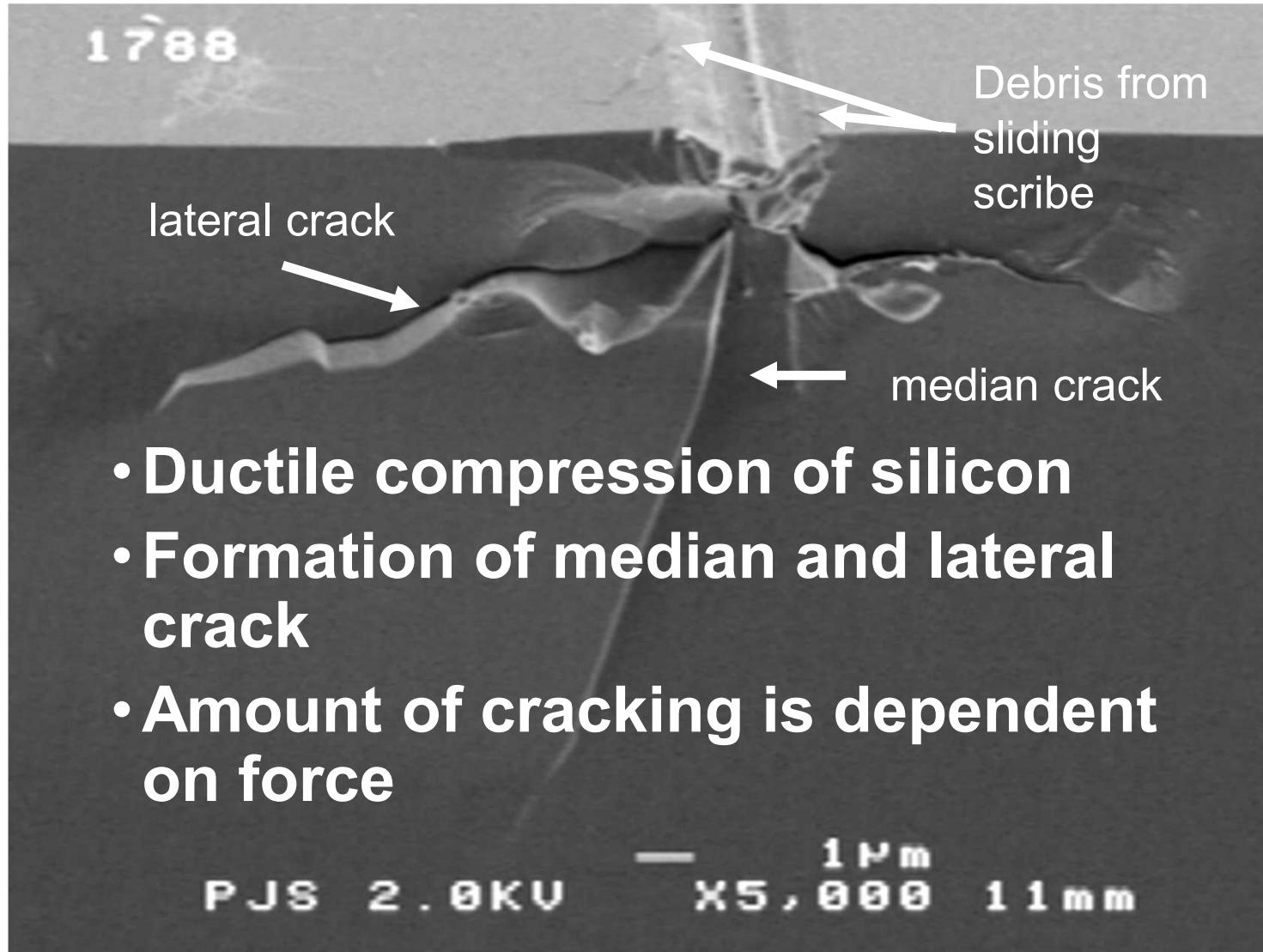


DESIGN OF EXPERIMENTS-PARTICLES





WHAT IS GOING ON DURING SCRIBING?





WHAT IS GOING ON DURING SCRIBING?

- Diamond tip creates a median crack underneath the scribe line

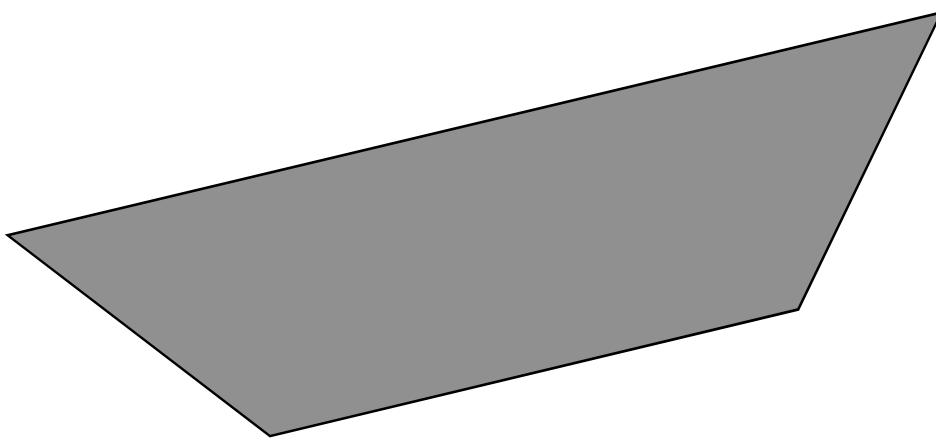
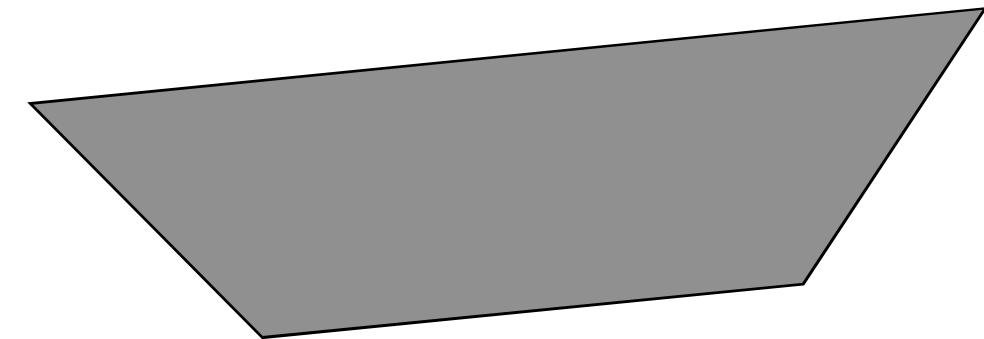
$$K = \sqrt{\frac{\text{crack_depth}}{2 \cdot \text{crack_radius}}}$$

- This creates a stress concentration at the crack tip
- At the tip, the crack radius is about 2 Å
- For a 20 um deep crack, this gives a stress concentration factor of 223

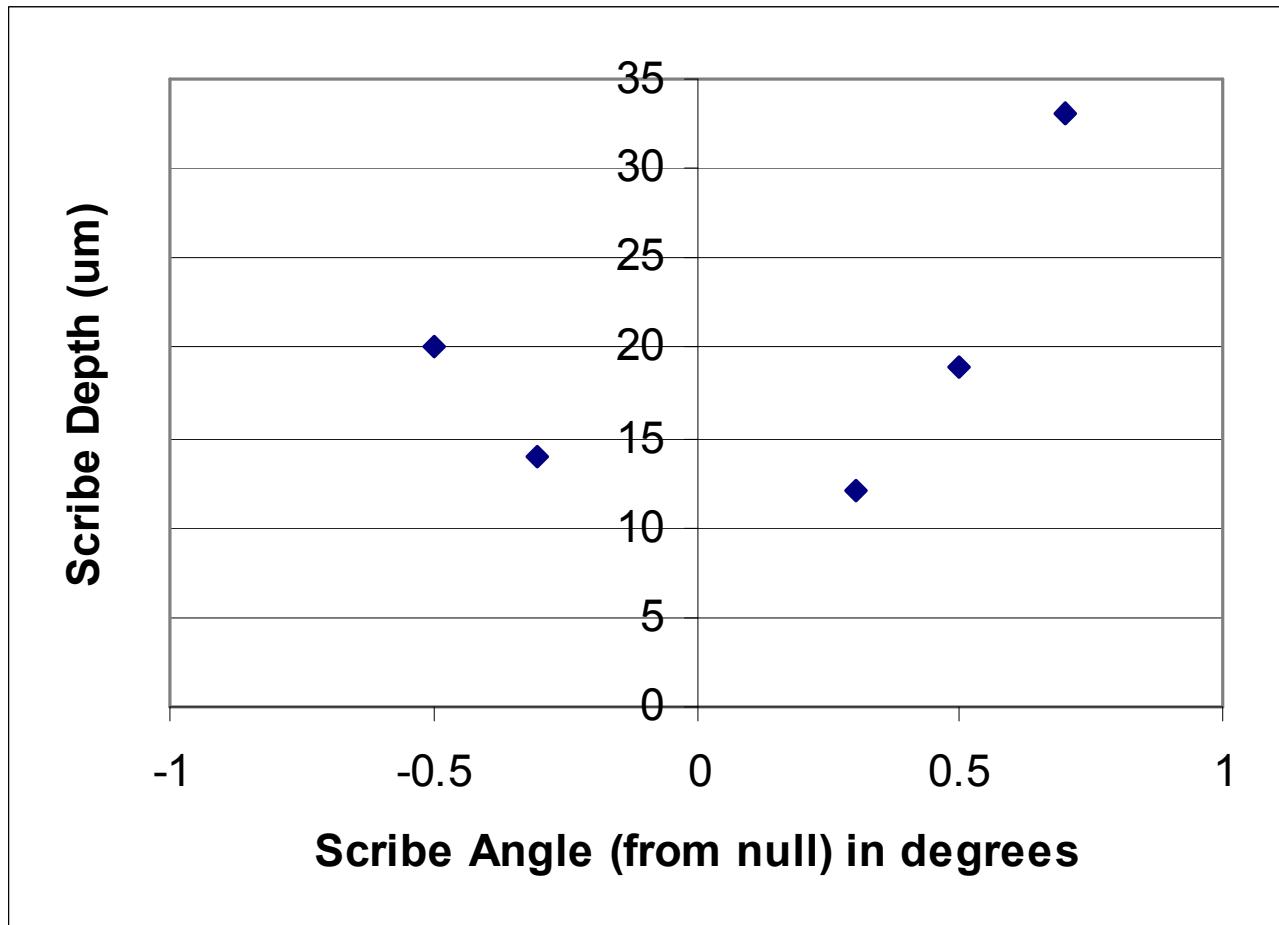


INFLUENCE OF SCRIBE ANGLE

- Shallow Angle
- Sharp Angle
- The sharper the angle the more material is displaced

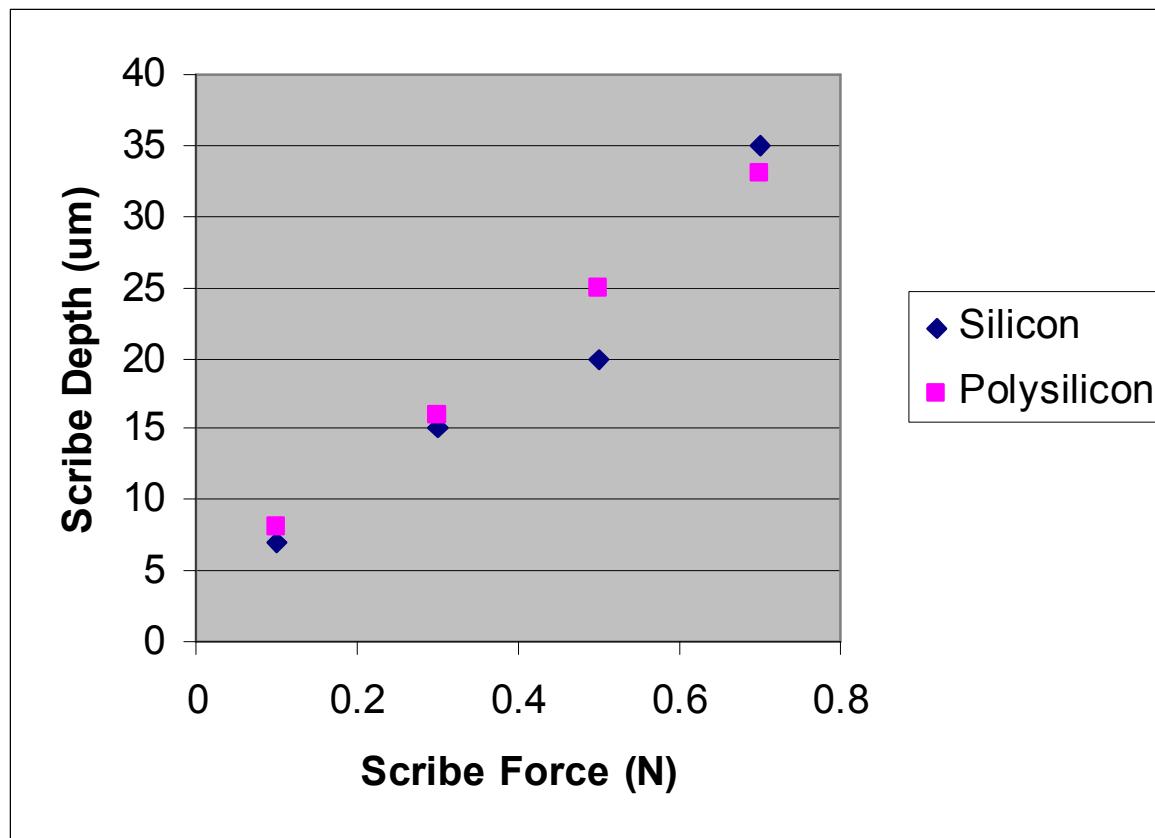


SCRIBE DEPTH VS SCRIBE ANGLE

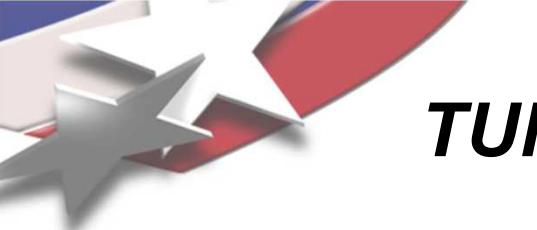




SCRIBING POLYSILICON VS SILICON

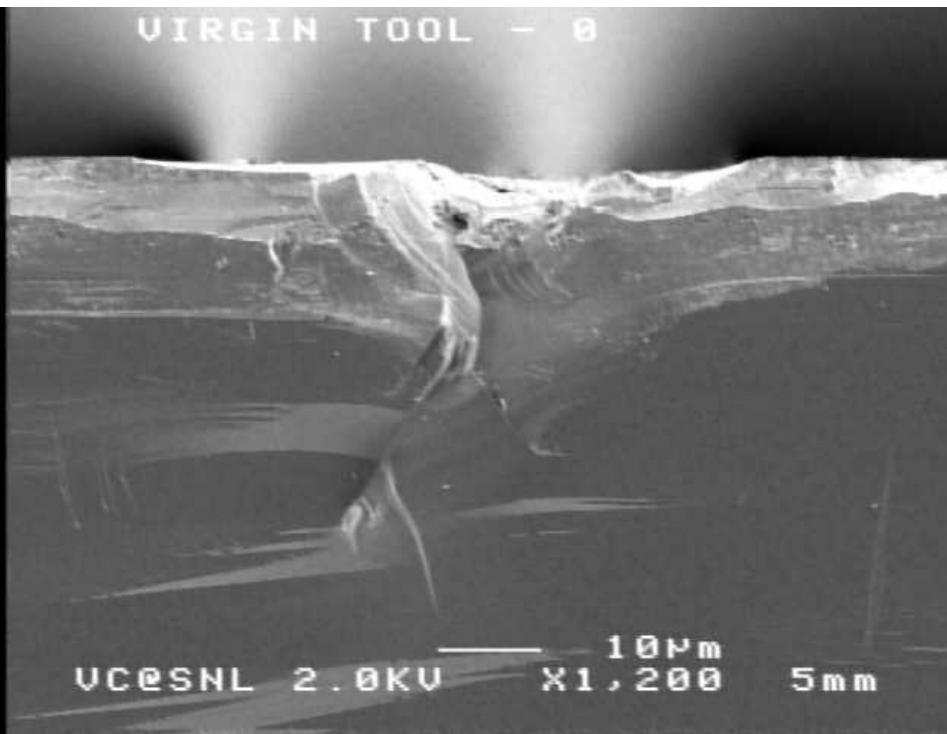


- The two films are roughly equivalent in terms of scribe performance

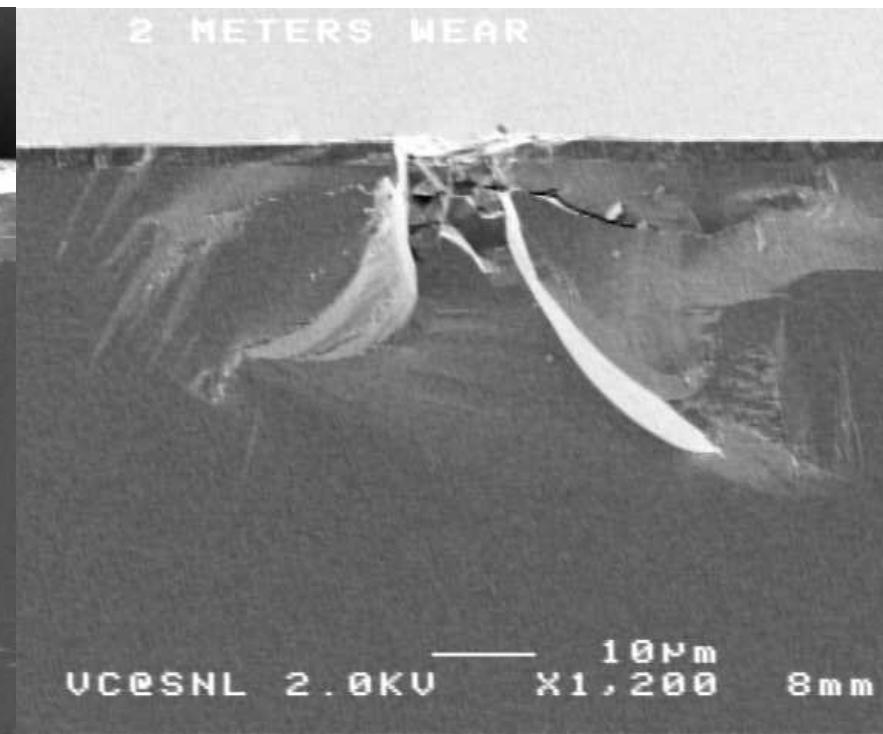


TUNGSTEN FILMS IN STREETS

VIRGIN TOOL - 0



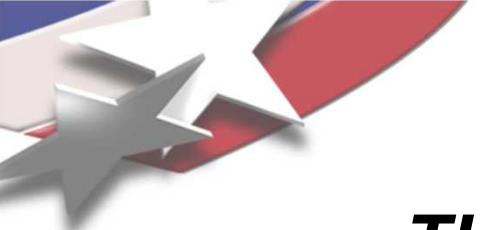
2 METERS WEAR



Initial

Tungsten thin film on silicon

2 meters of wear



TUNGSTEN FILMS IN STREETS

VIRGIN TUNG - 0-

UCesNL 2.0KU — 10 μ m X1,000

2 METERS WEAR

UCesNL 2.0KU — 10 μ m X1,900 10mm

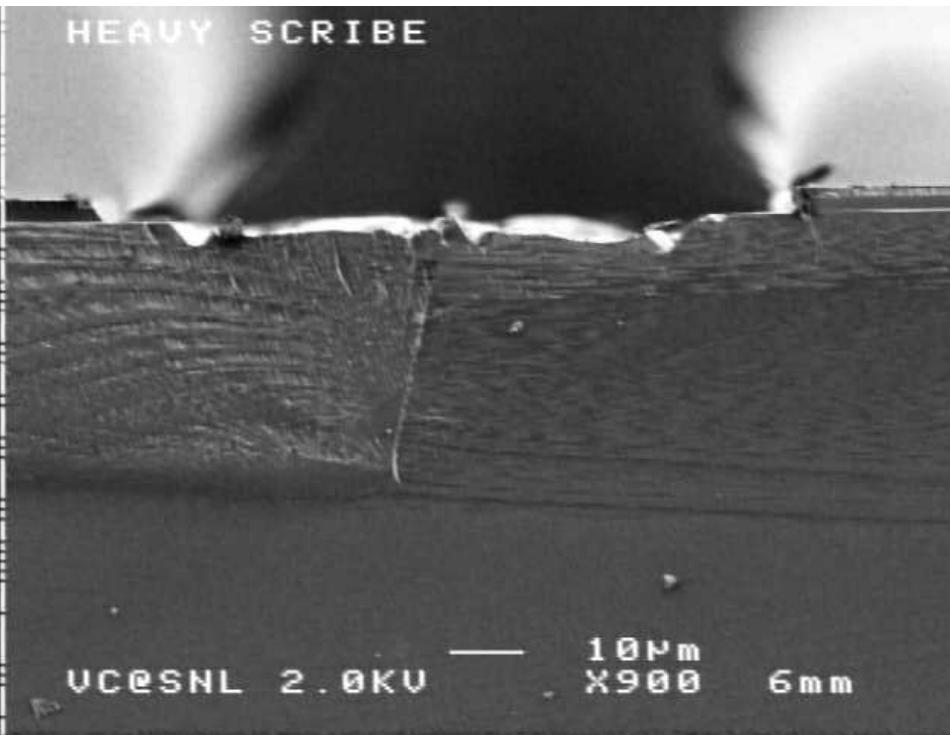
Initial

2 meters of wear



WEAR FROM Si_3N_4

HEAVY SCRIBE



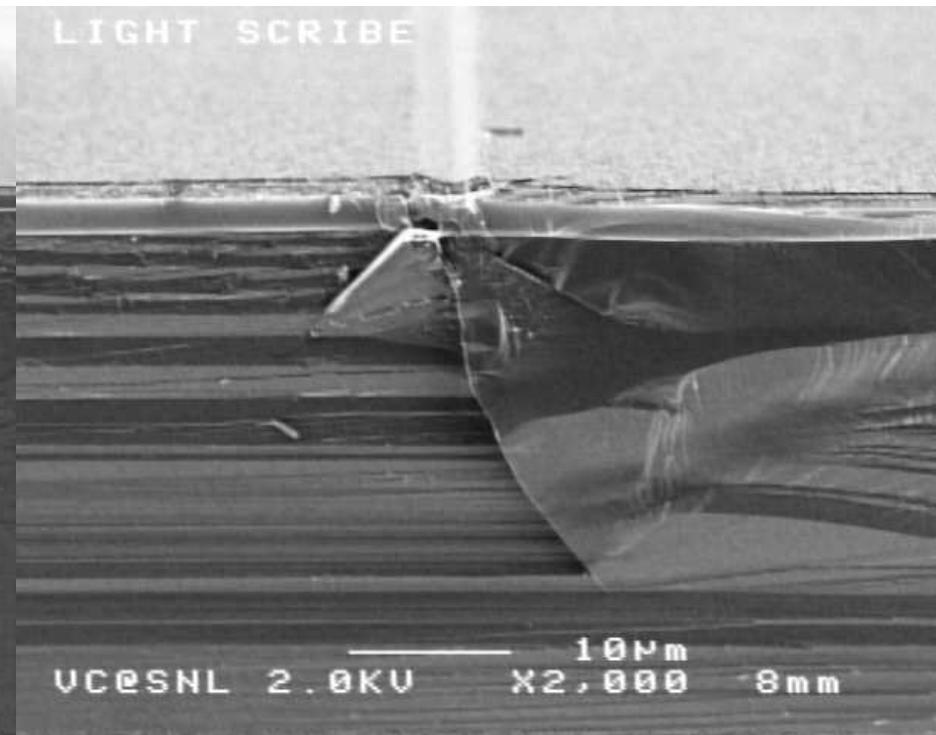
UCCSNL 2.0KU

10 μm

$\times 900$

6mm

LIGHT SCRIBE



UCCSNL 2.0KU

10 μm

$\times 2,000$

8mm

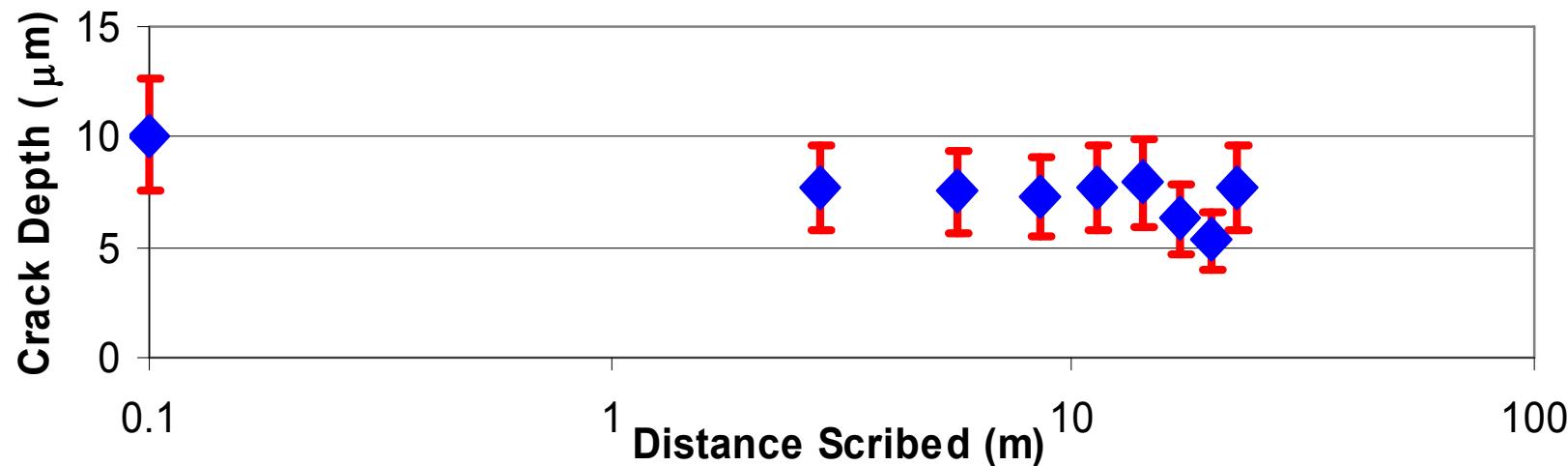
virgin scribe

After 1 meter of wear
(7 passes across the
wafer)

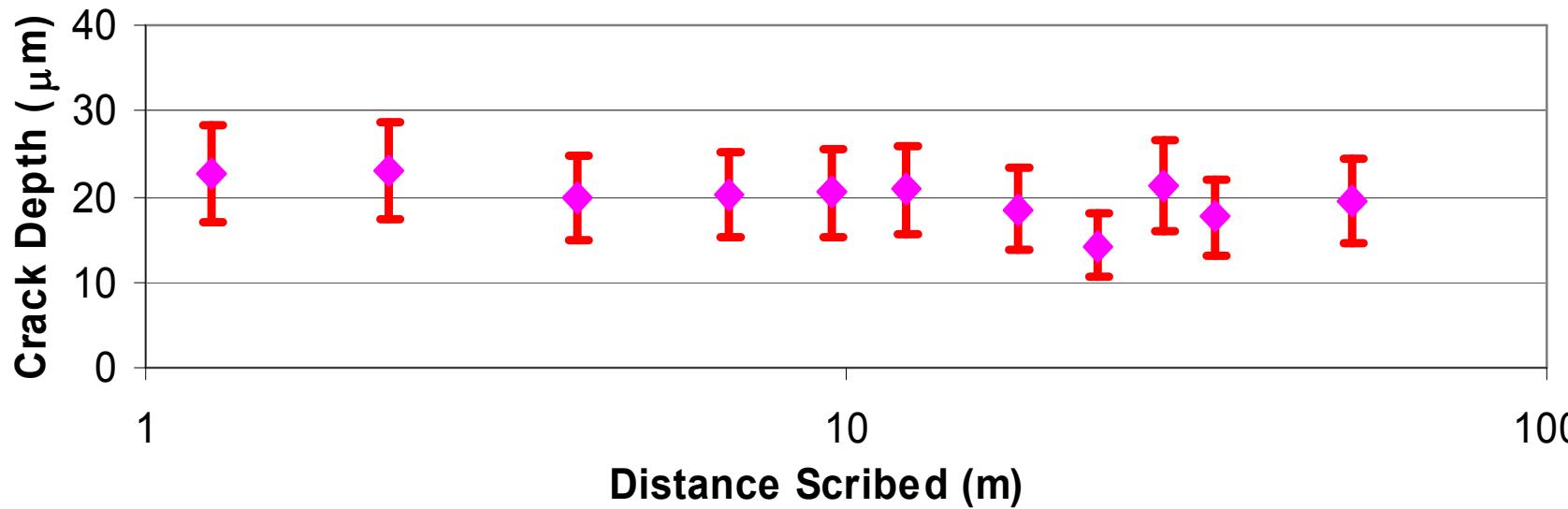


WEAR IN SCRIBE TIP ON SILICON

Minimal Scribe Force



High Scribe Force



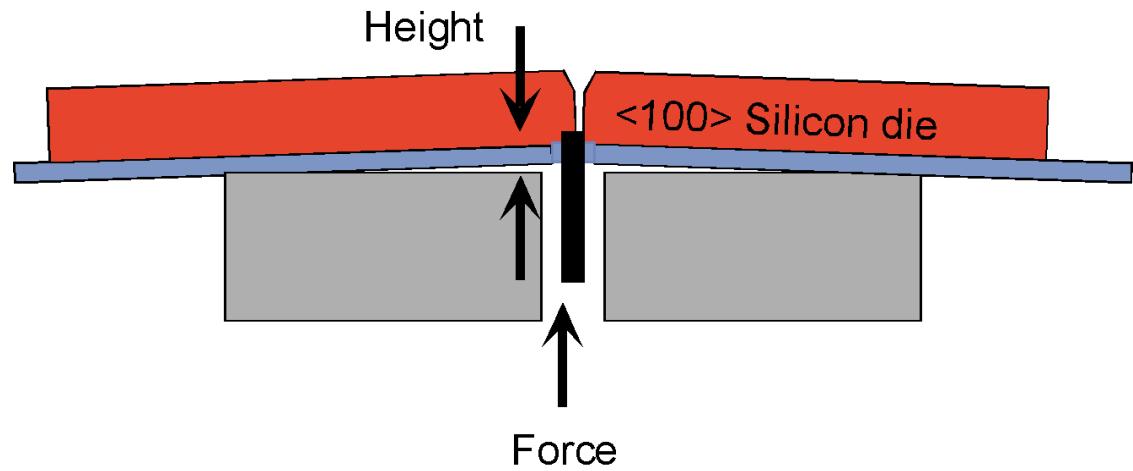


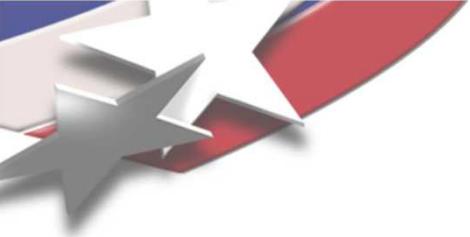
UNANSWERED QUESTION - WEAR

- The vendor recommends that the scribe tip be replaced when the wafers stop breaking or when the scribe line becomes faint
- Wear in the scribe tip is one source of inconsistency in an otherwise consistent process

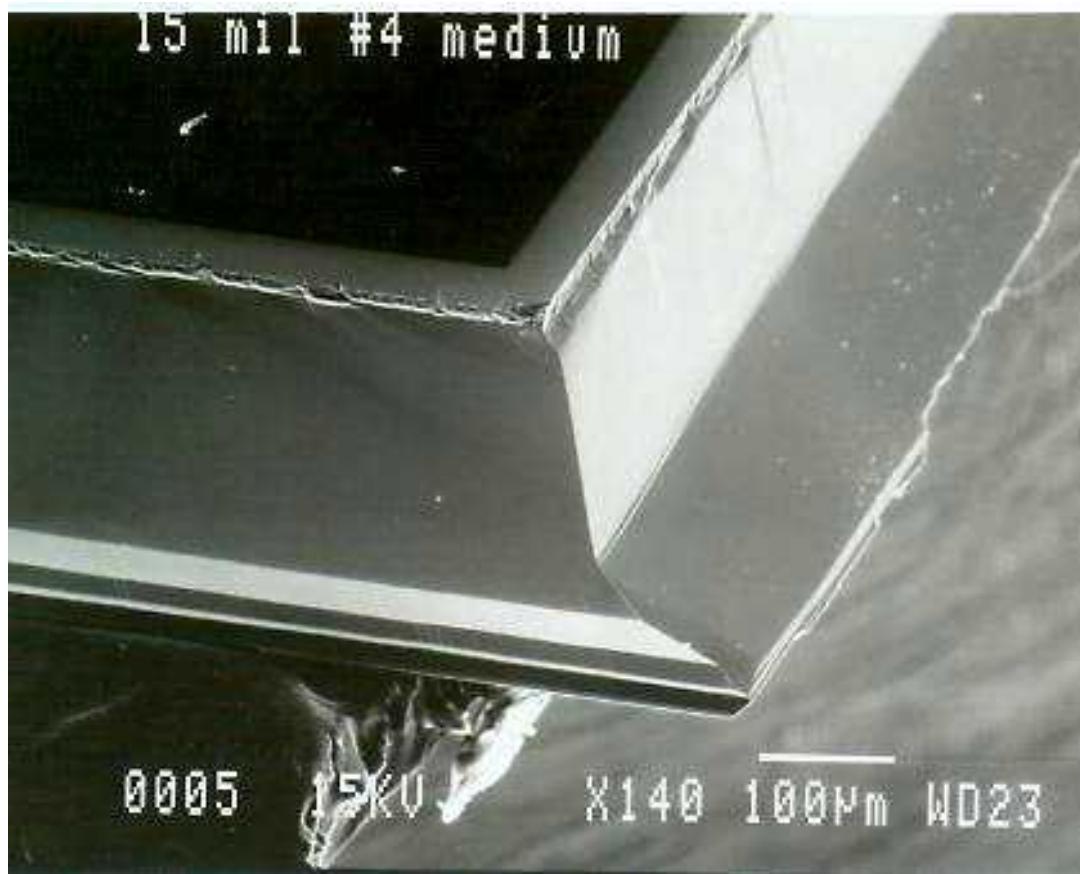
WHAT IS GOING ON DURING BREAKING?

- The wafer can be modeled as a simply supported plate
- The impulse bar can be modeled as an impulse function to the silicon wafer
- If the applied stress is high enough, the wafer cracks along the scribe line





CANTILEVER CURL

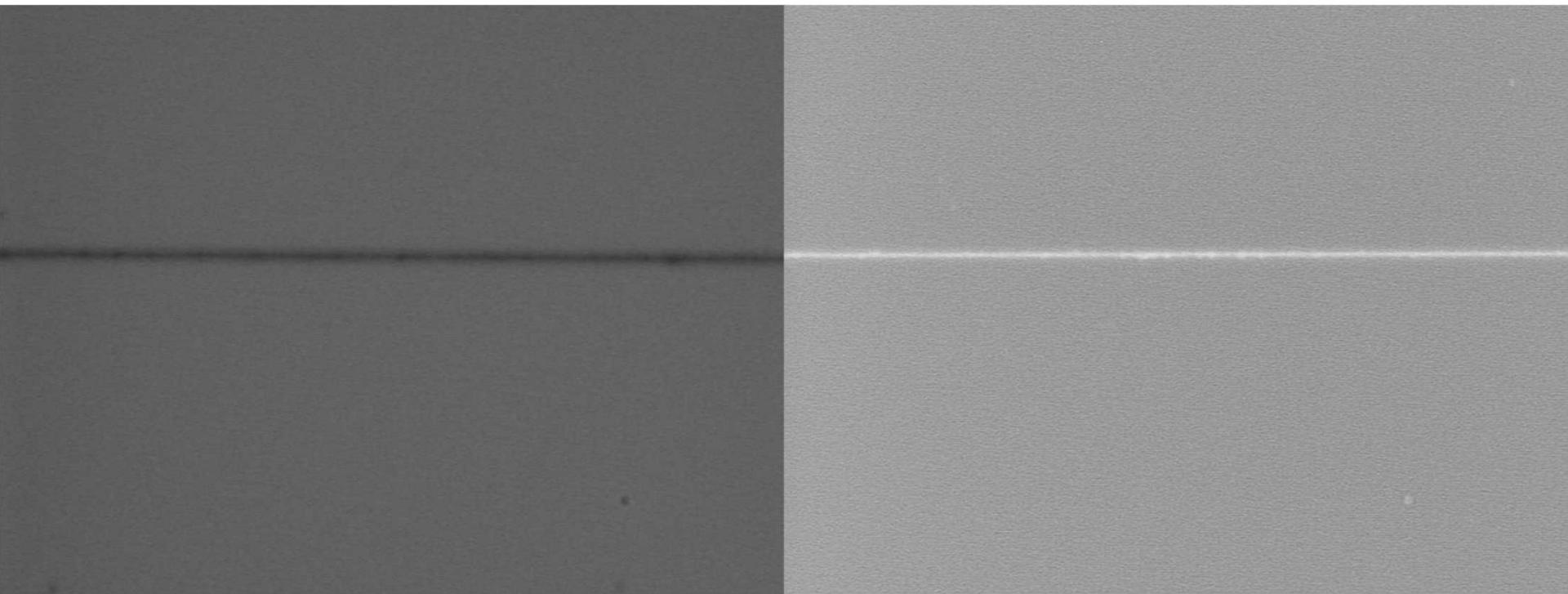


- Typical result
- by non ideal forces during breaking



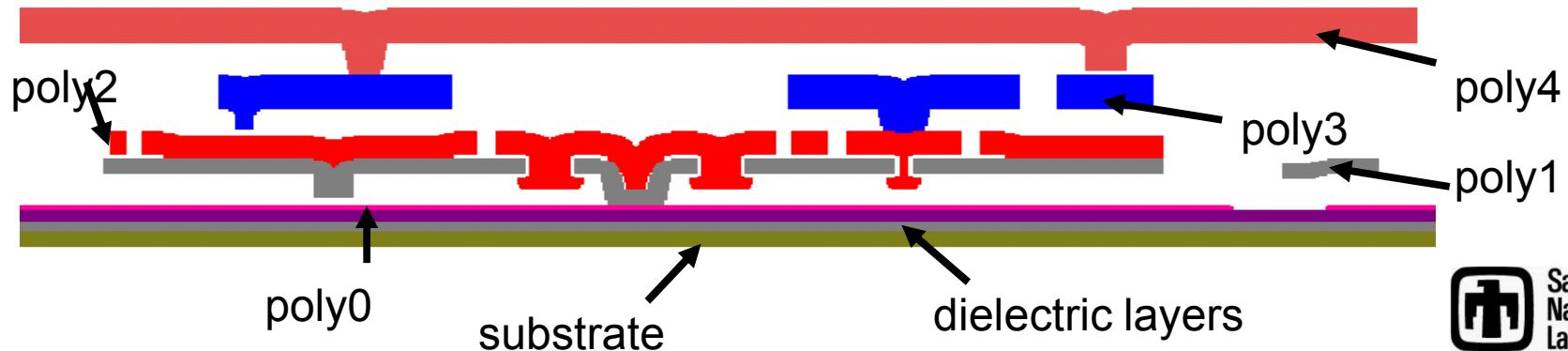
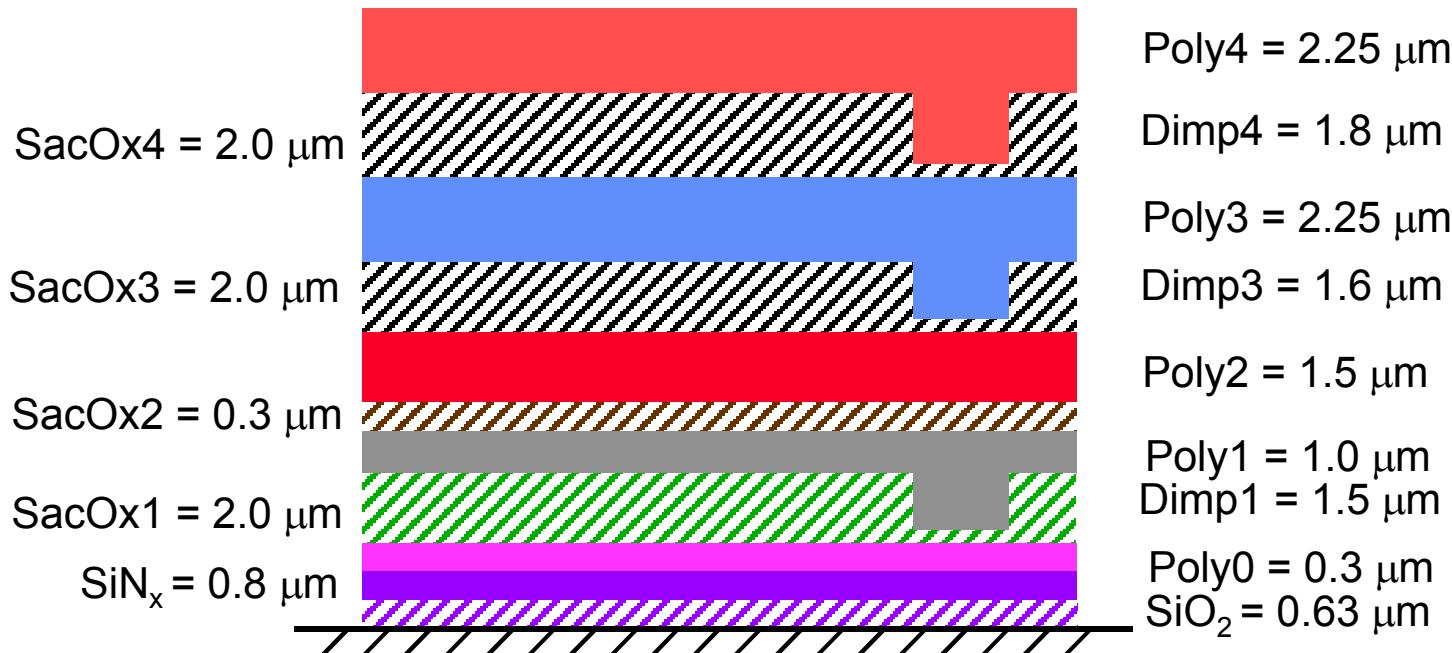
BUT DOES SCRIBING PRODUCE ~~PARTICLES?~~

- Scribe and break with optimized parameters



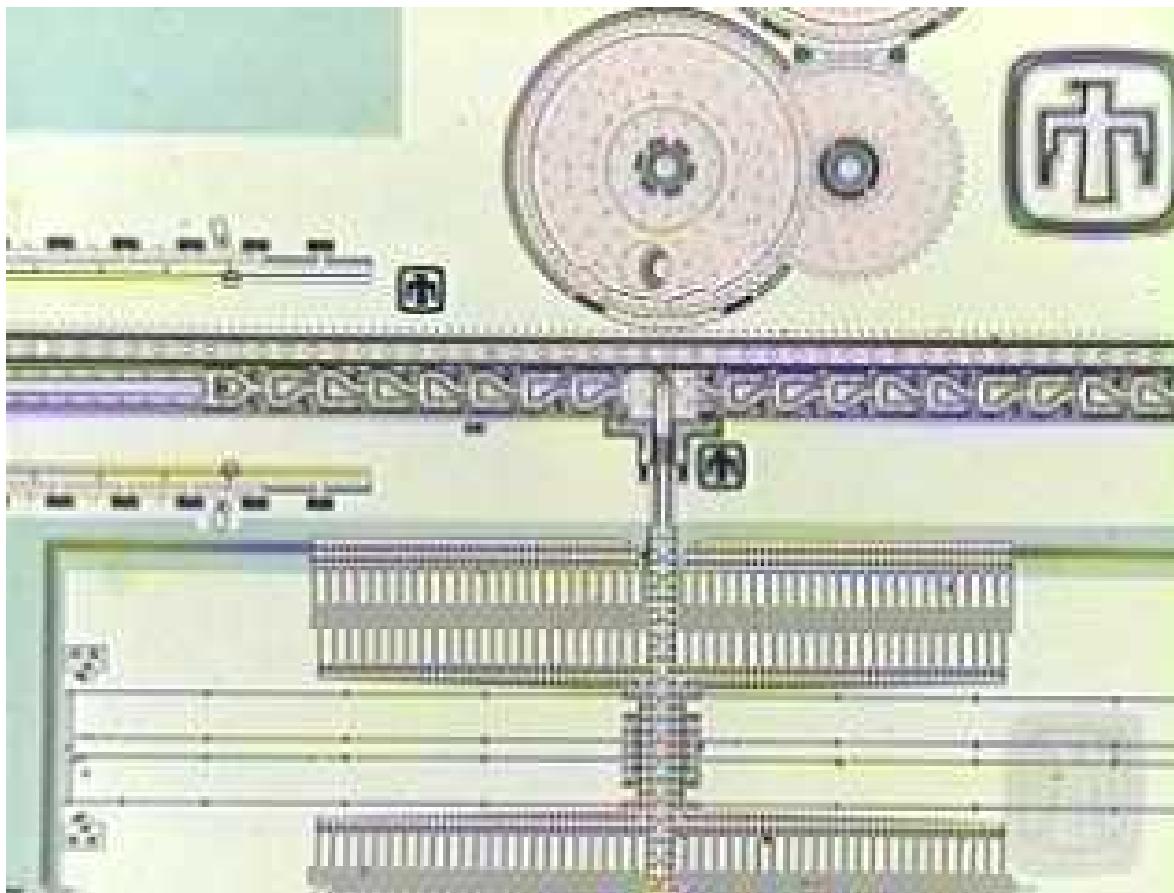
- 2 different scribe lines after break
- Field of view is about 1.1 mm x 1.1 mm

SURFACE MICROMACHINES





ELECTROSTATIC ACTUATORS

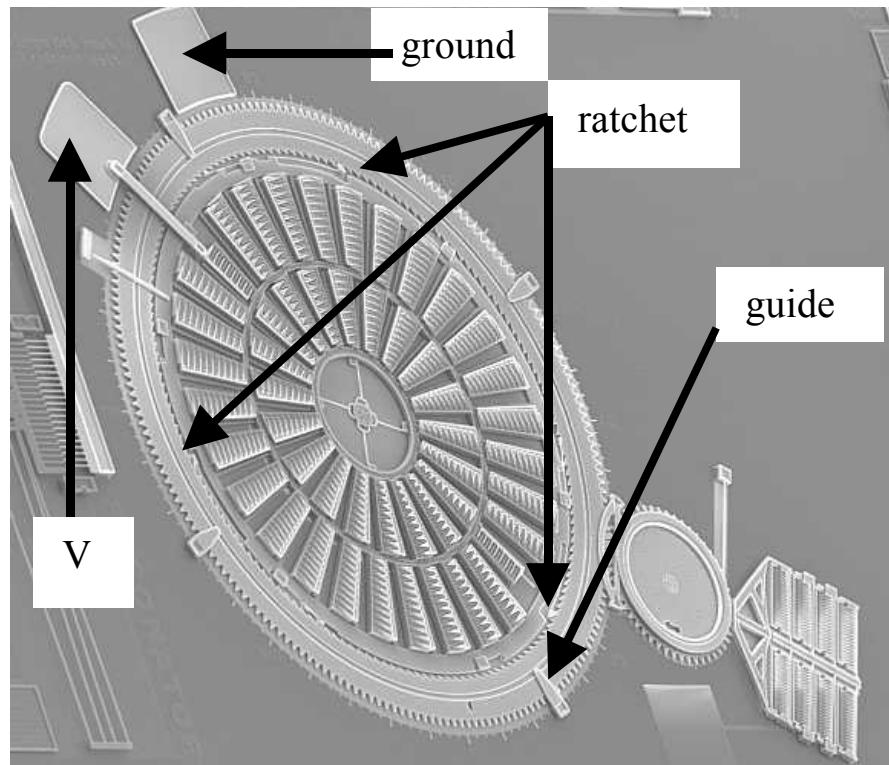
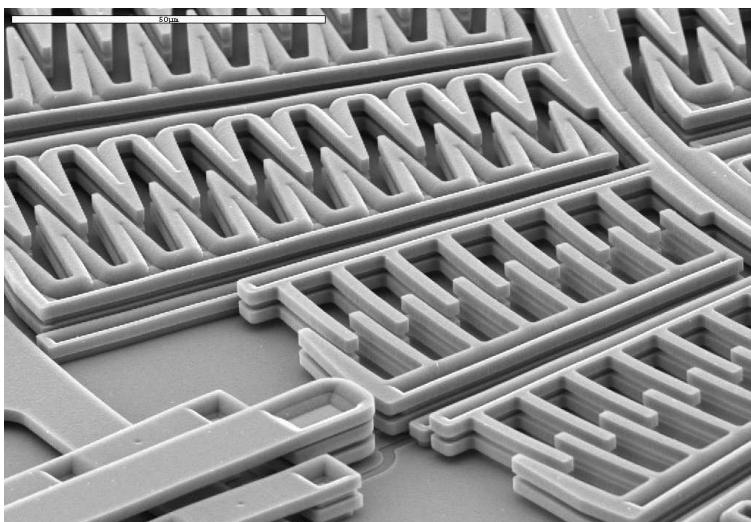


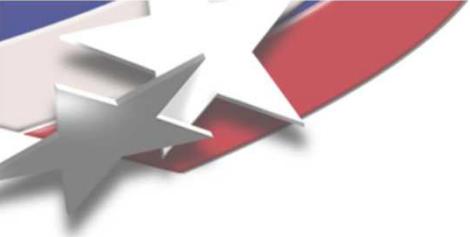
- Electrostatic actuators tend to attract particles



EXPERIMENTAL RESULTS

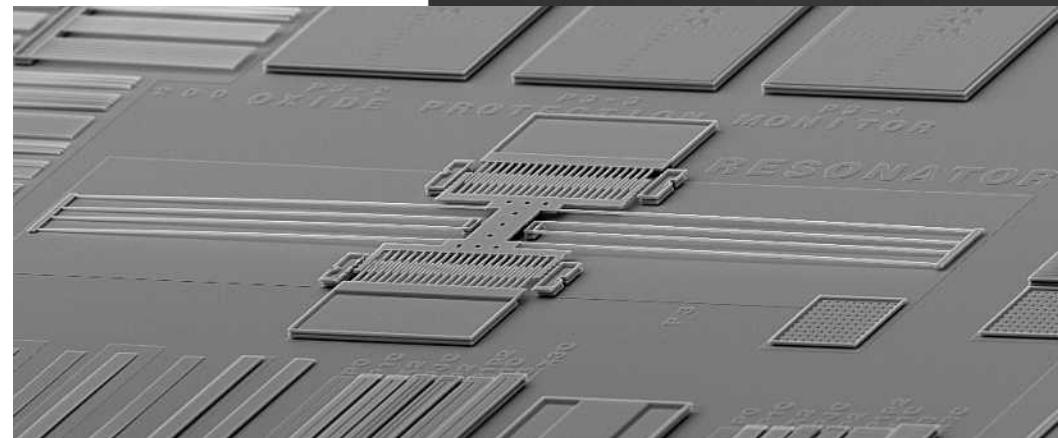
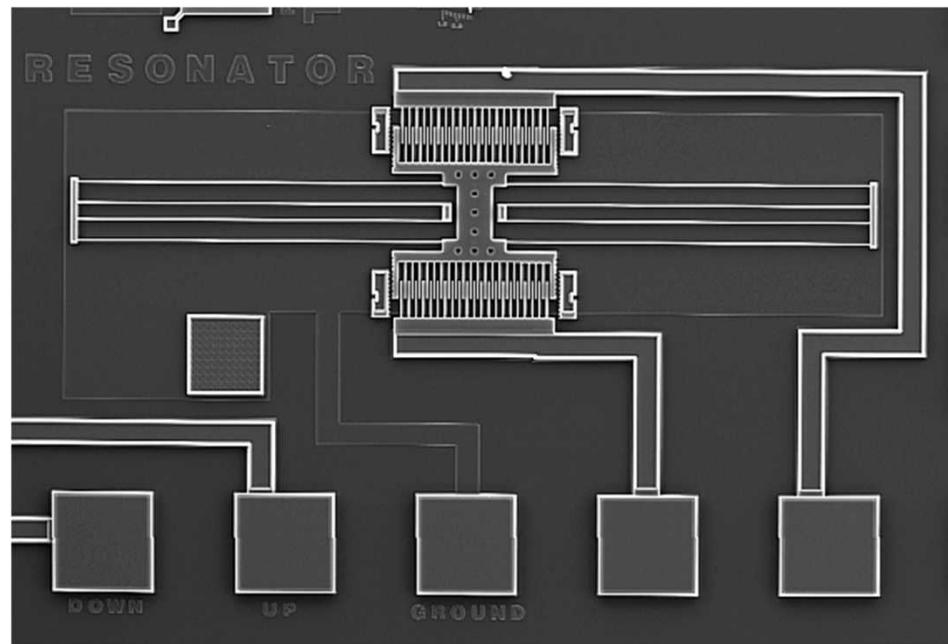
- 81% Yield on torsional ratcheting actuators (TRA)





EXPERIMENTAL RESULTS

- 98% yield on resonators





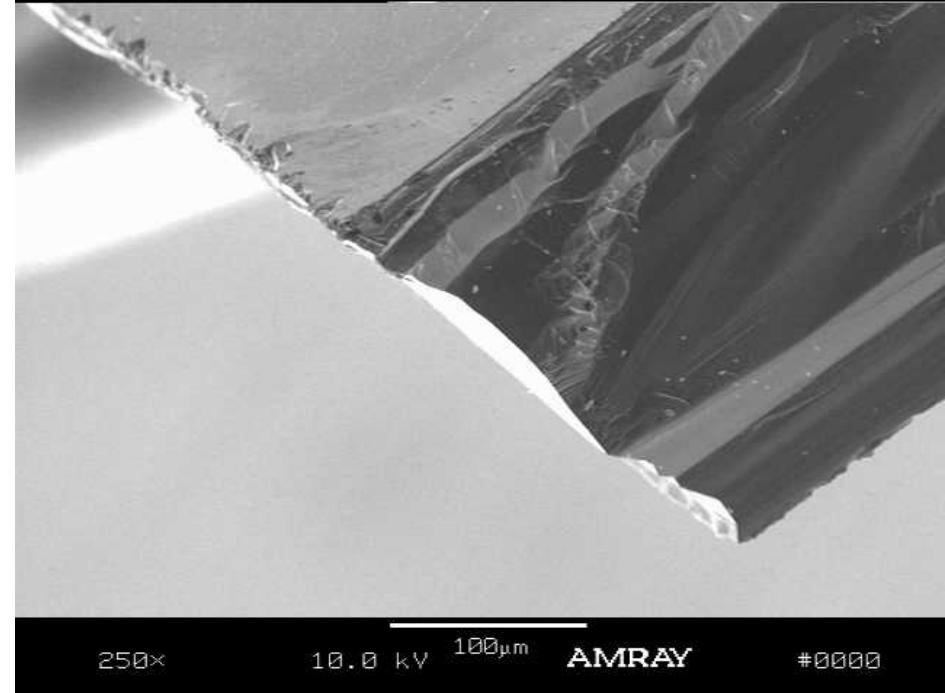
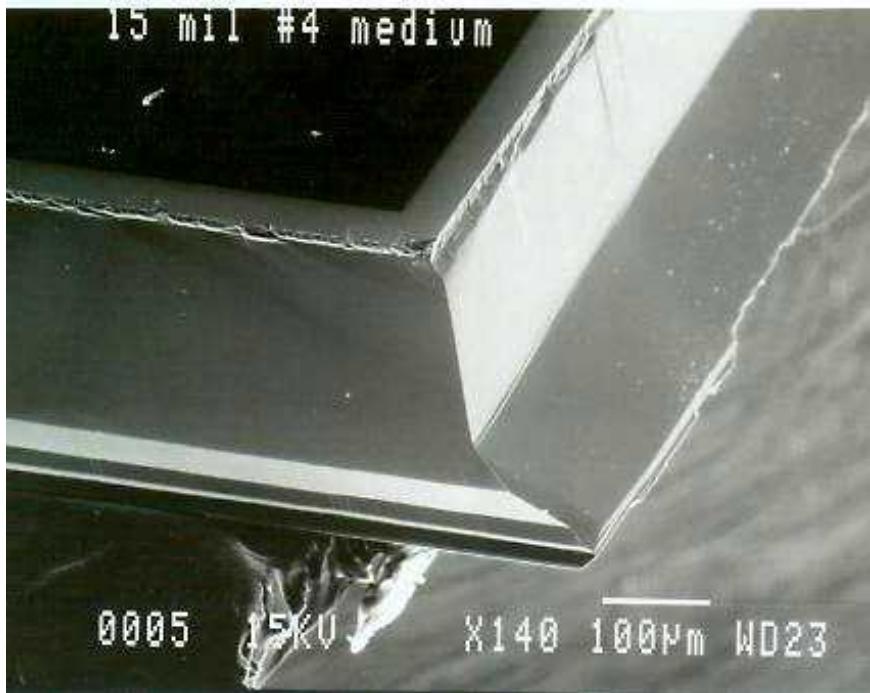
COMPARISONS TO OTHER TECHNIQUES

- Scribe and break is an appropriate and successful technique for enabling full wafer release for SUMMiT™ V.
- However, scribe and break has some limitations
 - The ratio of die size to wafer thickness must be at least 10 to 1
 - Scribe lines must follow the crystal plane
 - Incompatibility with silicon nitride and silicon dioxide and other surface coatings

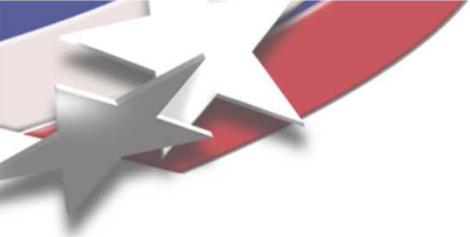




CANTILEVER CURL



- **Mostly caused by non-uniform pressure during the break**



CONCLUSIONS

- **Outline**
 - **Why**
 - this approach does work
 - **Yes, we know what is going on**
 - crack depth
 - design of experiments
 - **Yes it works**
 - Micromachines yield after scribe and break
- **Discuss future work**



ACKNOWLEDGEMENTS

- **Regan Stinnett, David Plummer, Mike Rightley, and Thom Fischer for funding this work**
- **Simone Smith for her processing expertise**
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- **Pat Shea and Bonnie McKenzie for the SEM images**
- **Jeremy Favia, Casey Stromer, Greg Alexander, and the rest of the staff of Dynatex International**
- **Rajan Tandon, Jill Glass, and Fernando Bitsie**